

## N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
60	0.16 at $V_{GS} = 10$ V	2.0
	0.22 at $V_{GS} = 4.5$ V	1.7

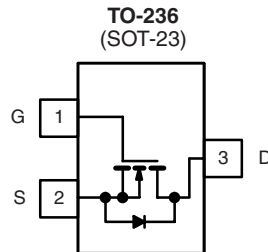
### FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET
- 100 %  $R_g$  Tested



Available  
**RoHS\***  
COMPLIANT

HALOGEN  
**FREE**  
Available



Top View  
Si2308DS (A8)\*  
\* Marking Code

**Ordering Information:** Si2308DS-T1  
Si2308DS-T1-E3 (Lead (Pb)-free)  
Si2308DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	2.0
		$T_A = 70$ °C	1.6
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	10	A
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	1.0	
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	1.25
		$T_A = 70$ °C	0.80
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	100	°C/W
Maximum Junction-to-Ambient <sup>c</sup>		166	

Notes:

- Surface Mounted on FR4 board,  $t \leq 5$  s.
- Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 board.

For SPICE model information via the Worldwide Web: [www.vishay.com/www/product/spice.htm](http://www.vishay.com/www/product/spice.htm)

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

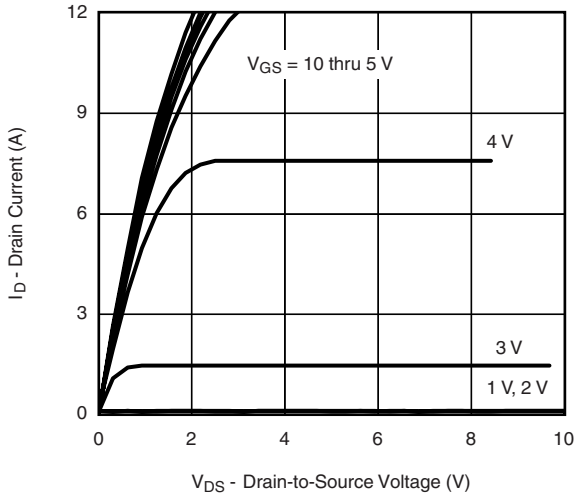
<b>MOSFET SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.5		3.0	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			0.5	$\mu\text{A}$
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 4.5\text{ V}, V_{GS} = 10\text{ V}$	6			A
		$V_{DS} \geq 4.5\text{ V}, V_{GS} = 4.5\text{ V}$	4			
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 2.0\text{ A}$		0.125	0.16	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 1.7\text{ A}$		0.155	0.22	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 4.5\text{ V}, I_D = 2.0\text{ A}$		4.6		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 1\text{ A}, V_{GS} = 0\text{ V}$		0.77	1.2	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 2.0\text{ A}$		4.8	10	nC
Gate-Source Charge	$Q_{gs}$			0.8		
Gate-Drain Charge	$Q_{gd}$			1.0		
Gate Resistance	$R_g$		0.5		3.3	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		240		$\mu\text{F}$
Output Capacitance	$C_{oss}$			50		
Reverse Transfer Capacitance	$C_{rss}$			15		
<b>Switching</b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 30\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 6\text{ }\Omega$		7	15	ns
Rise Time	$t_r$			10	20	
Turn-Off Delay Time	$t_{d(off)}$			17	35	
Fall Time	$t_f$			6	15	

Notes:

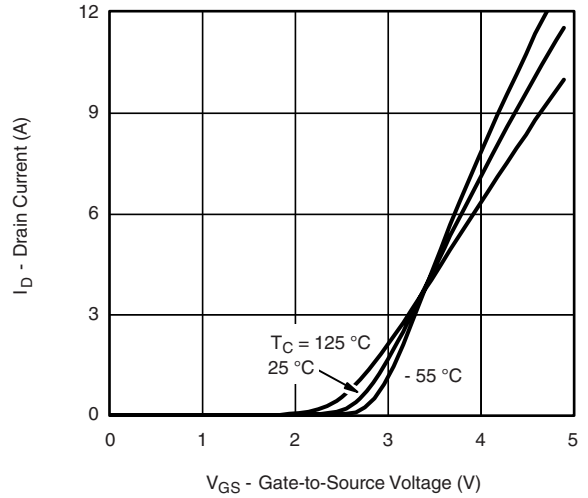
a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

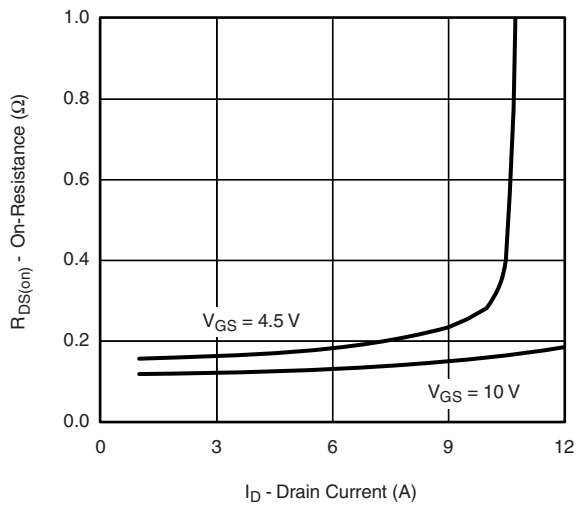
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



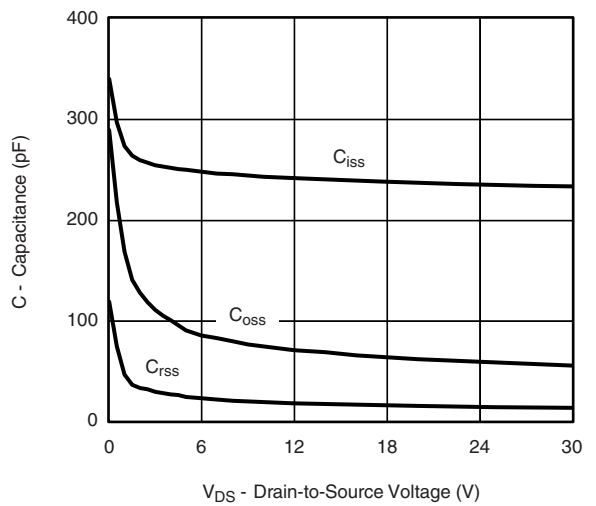
**Output Characteristics**



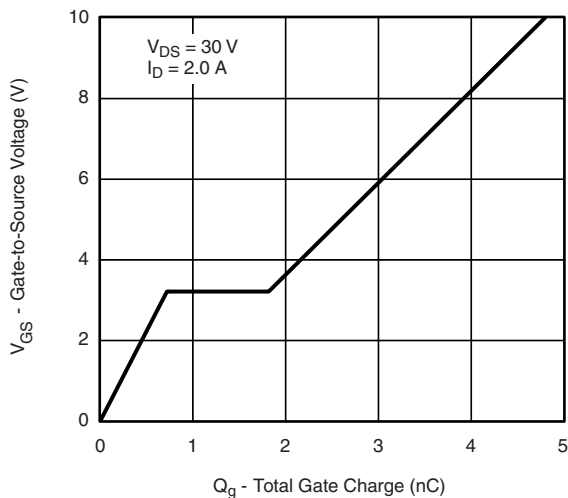
**Transfer Characteristics**



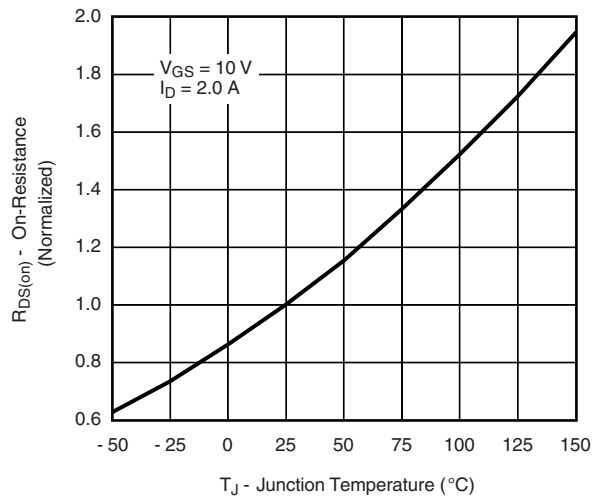
**On-Resistance vs. Drain Current**



**Capacitance**

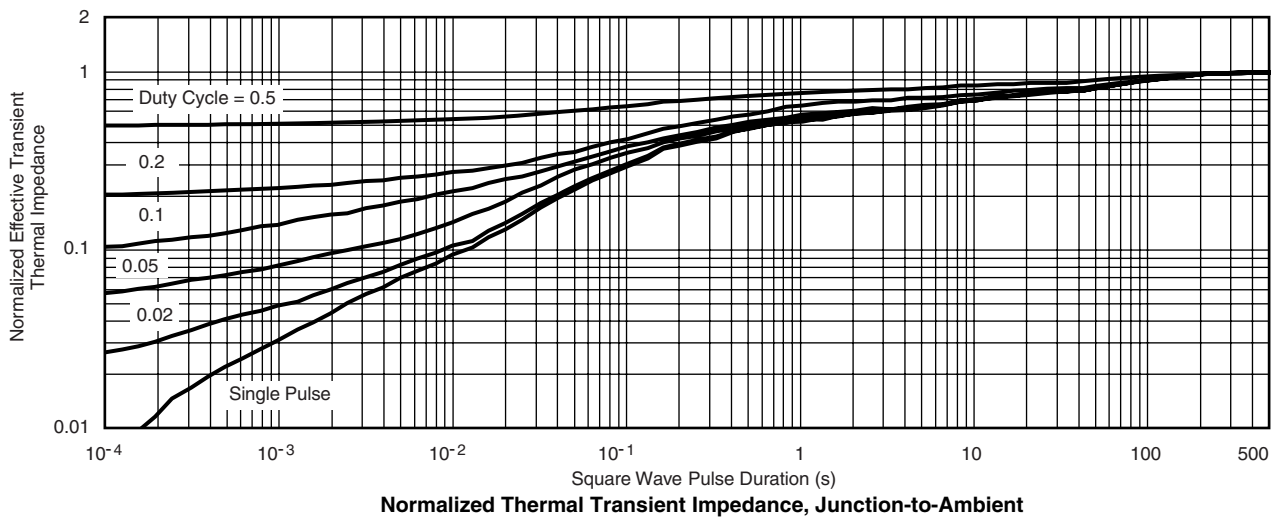
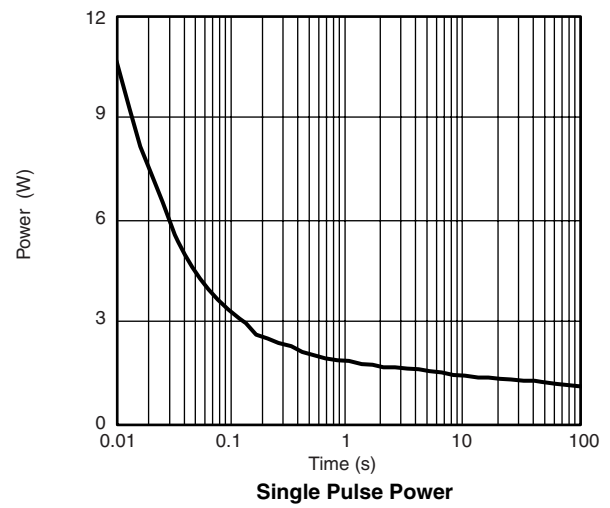
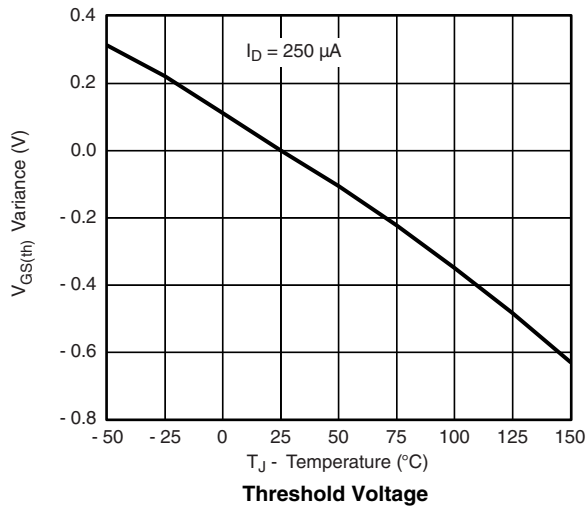
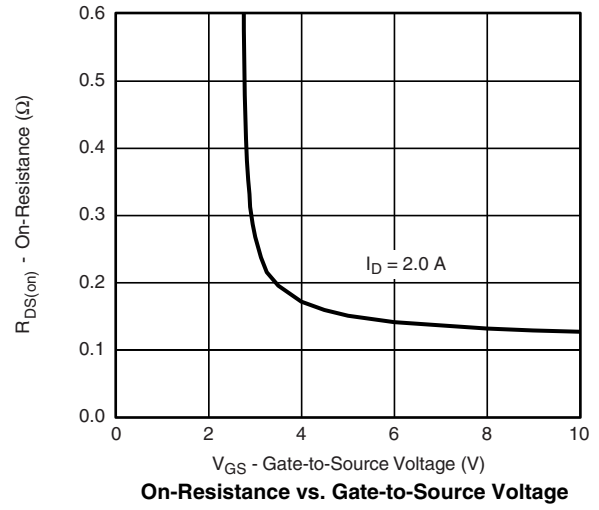
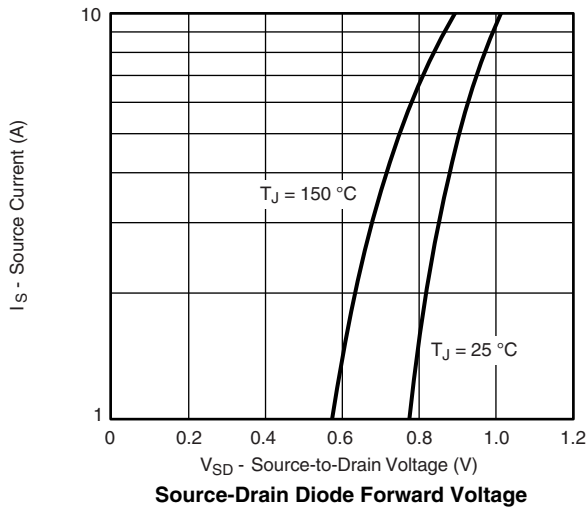


**Gate Charge**



**On-Resistance vs. Junction Temperature**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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